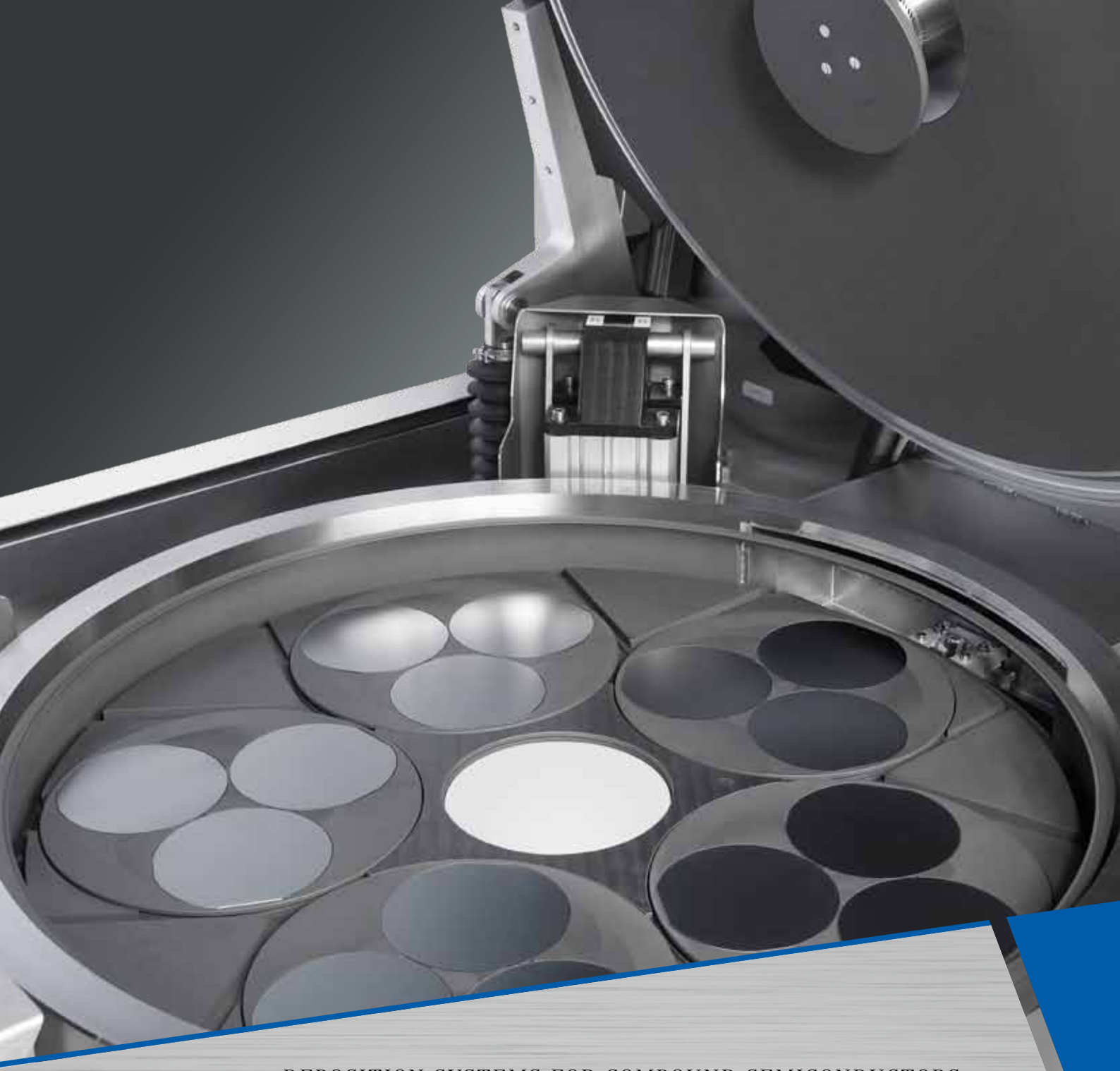


DEPOSITION SYSTEMS FOR COMPOUND SEMICONDUCTORS

AIX 2800G4-TM

for GaAs/InP based Optoelectronics and p-HEMT/HBT Devices

AIXTRON

Our technology. Your future.

Increase your capacity and take advantage of highest Yield

AIX 2800G4-TM MOCVD System

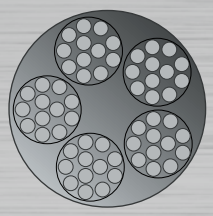
Your Benefit

- Highest device yield & throughput
- High precursor & hydride efficencies
- Lowest cost/wafer
- Flexible configuration for 2 to 8 inch

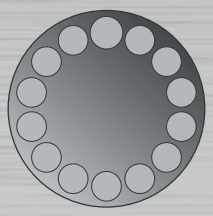
Design Highlights

- Automated satellite loading
- Triple gas injector
- Latest reactor design featuring
  - Advanced process tuning
  - Increased process robustness
  - Minimized overall maintenance

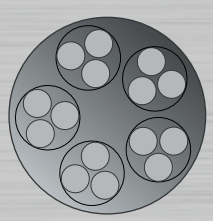
Available Susceptor Configurations



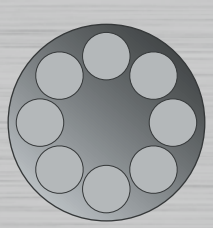
60x2 inch



14x3 inch



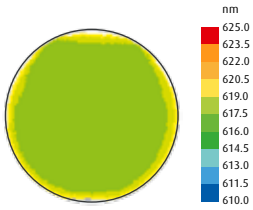
15x4 inch



8x6 inch

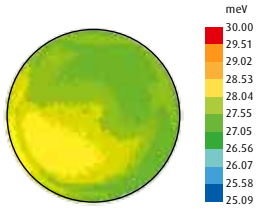
Process and Transfer Module

4 inch ALGaInP MQW results



PL wavelength uniformity (Avg. 617nm)

0.6 nm standard deviation without EE



FHWM uniformity (Avg. 27meV)

1.7 % standard deviation without EE

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